NSN 5961-01-105-8549

Unitized Semiconductor Devices - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-105-8549 **Inclosure Material:** Ceramic **Overall Length:** Between 0.660 inches and 0.785 inches **Overall Height:** 0.325 inches **Overall Width:** 0.325 inches **Component Name And Quantity:** 4 transistor **Mounting Method:** Press fit **Features Provided:** Hermetically sealed case **Semiconductor Material:** Silicon all transistor **Voltage Rating In Volts Per Characteristic:** 70.0 collector to base voltage, dc all transistor and 445.0 collector to emitter voltage, dc all transistor and 6.0 emitter to base voltage, dc all transistor **Current Rating Per Characteristic:** 1.50 amperes source cutoff current all transistor **Maximum Operating Tempurature Per Measurement Point:** 200.0 degrees celsius junction **Special Features:** All transistor junction pattern arrangement: npn **Terminal Type And Quantity:** 14 ribbon Shelf Life: N/a **Unit Of Measure: Demilitarization:** No Fiig: A110a0